Unit: mm



TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSⅢ)

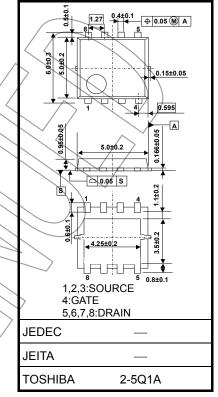
TPCA8102

Lithium Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance: R_{DS} (ON) = 4.5m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 60S$ (typ.)
- Low leakage current: $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode: V_{th} = -0.8 to -2.0 V (V_{DS} = -10 V, I_D = -1 mA)

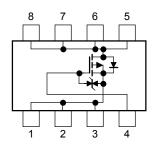
Characte	ristics	Symbol	Rating	Unit
Drain-source voltage		VDSS	-30	V
Drain-gate voltage (F	R _{GS} = 20 kΩ)	V _{DGR}	-30	V
Gate-source voltage		VGSS	±20	X
Drain current	DC (Note 1)	Ъ	-40	A
	Pulsed (Note 1)	e 1) IDP -120	-120	
Drain power dissipati	on (Tc=25°C)	PD	45	W
Drain power dissipation (t = 10 s) (Note 2a)		PD	2.8	W
Drain power dissipati	on (t ≠ 10 s) (Note 2b)	PD	1,6	W
Single pulse avalanche energy (Note 3).		Eas	208	mJ
Avalanche current		TAR	- 40	А
Repetitive avalanche energy (Tc=25°C) (Note 4)		EAR	4.5	mJ
Channel temperature			150	°C
Storage temperature	range	T _{stg}	-55 to 150	°C

Α



Weight: 0.076 g (typ.)

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

Using continuously under/heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

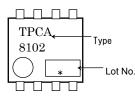
This transistor is an electrostatic-sensitive device. Please handle with caution.

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Thermal Characteristics

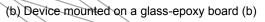
Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case (Tc=25°C)	R _{th (ch-c)}	2.78	°C/W	
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W	

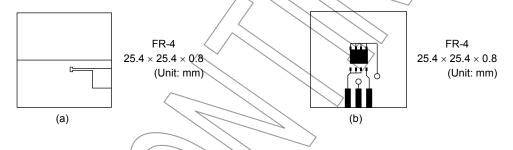
Marking (Note 5)



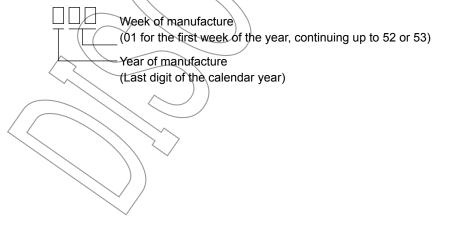
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)





- Note 3: $V_{DD} = 24 \text{ V}, T_{ch} = 25^{\circ}\text{C}$ (initial), $L = 100 \mu \text{ H}, R_{G} = 25 \Omega, I_{AR} = -40 \text{ A}$
- Note 4: Repetitive rating: pulse width limited by max channel temperature
- Note 5: "O" on the lower left of the marking indicates Pin 1.
 - * Weekly code (three digits):

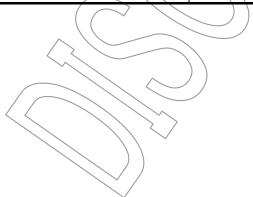


Electrical Characteristics (Ta = 25°C)

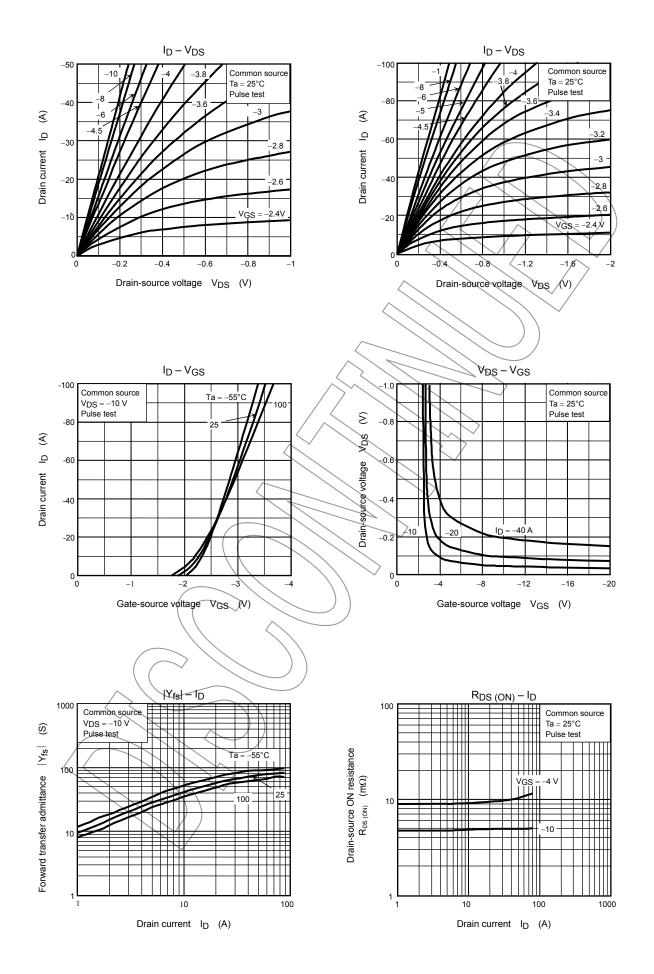
Ch	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cui	rent	I _{GSS}	$V_{GS}=\pm 16~V,~V_{DS}=0~V$	_		±10	μA
Drain cut-OFF cu	ırrent	I _{DSS}	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	_	-10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = -10$ mA, $V_{GS} = 0$ V	-30	_		V
		V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-15			v
Gate threshold ve	oltage	V _{th}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	0.8	\bigwedge	-2.0	V
Drain-source ON resistance		R _{DS (ON)}	$V_{GS} = -4 \text{ V}, I_D = -20 \text{ A}$	X	9.0	14	mΩ
			$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -20 \text{ A}$	X	4.5	6.0	
Forward transfer	admittance	Y _{fs}	$V_{DS} = -10 V, I_D = -20 A$	30	60	(\neq)	S
Input capacitance		C _{iss}		/-/	4600	$\langle -$	
Reverse transfer capacitance		C _{rss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	$\langle \cdot \rangle$	850	>-	pF
Output capacitance		C _{oss}		$\langle \cdot \rangle$	980	_	
Switching time	Rise time	tr	V_{GS} V_{T} V_{GS} V_{T}	F	10	—	
	Turn-ON time	t _{on}		$\sum_{i=1}^{n}$	20	_	
	Fall time	t _f	4 m 0 L	>-	78	_	ns
	Turn-OFF time	toff	V _{DD} ≟ -15 V Duty≦ 1%, t _w = 10 µs	_	220		
Total gate charge (gate-source plus		Qg	$V_{DD} \simeq -24 \text{ V}, V_{GS} = 10 \text{ V},$		109		
Gate-source charge 1		Qgs1	$I_{D} = -40 \text{ A}$	—	24	_	nC
Gate-drain ("miller") charge		Qgd		_	25		

Source-Drain Ratings and Characteristics (Ta = 25°C)

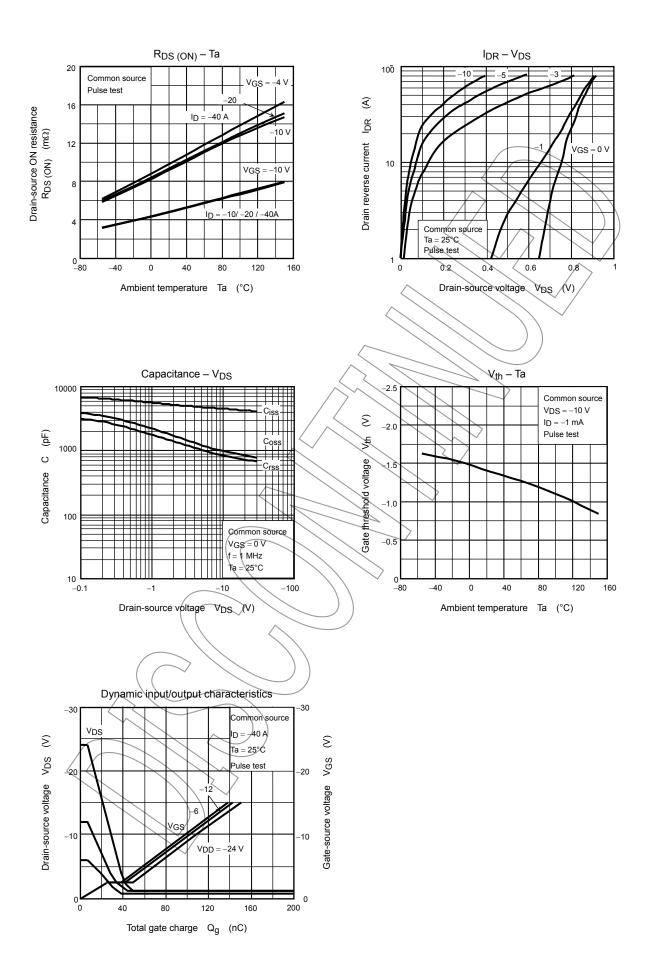
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pul	se (Note 1)	HORP	-		_	-120	А
Forward voltage (diode)		VDSF	$I_{DR} = -40 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$	_	_	1.2	V

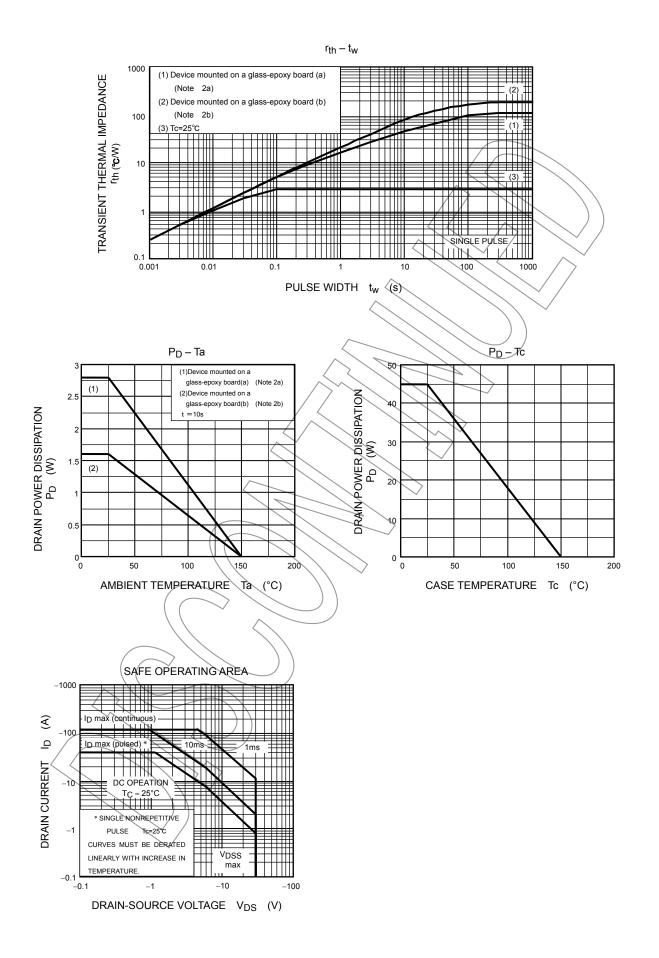


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